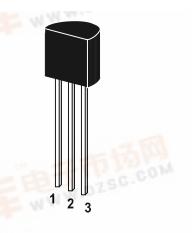
ST 2SC1740 查询"2SC1740"供应商

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into four groups Q, R, S and E. according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25℃)

Collector Base Voltage Collector Emitter Voltage	V _{CBO}	60 60	V
Collector Emitter Voltage			
5	V _{CEO}	50	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	Ic	150	mA
Power Dissipation	P _{tot}	300	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 to +150	°C



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 07/12/2002

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Characteristics at T_{amb} =25 ^{o}C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at V _{CE} =6V, I _C =1mA	Q	h_{FE}	120	-	270	-
	R	h_{FE}	180	-	390	-
	S	h _{FE}	270	-	560	-
	Е	h_{FE}	390	-	820	-
Collector Base Breakdown Voltage						
at I _C =50μA		$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage						
at I _C =1mA		$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage						
at I _E =50μA		$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current						
at V _{CB} =60V		I _{CBO}	-	-	0.1	μA
Emitter Cutoff Current						
at V _{EB} =5V		I_{EBO}	-	-	0.1	μA
Collector Saturation Voltage						
at I _C =50mA, I _B =5mA		$V_{\text{CE(sat)}}$	-	-	0.4	V
Gain Bandwidth Product						
at V_{CE} =12V, I _C =2mA		f _T	-	180	-	MHz
Output Capacitance						
at V_{CB} =12V, f=1MHz		C _{OB}	-	2	3.5	pF







Dated : 07/12/2002